

Volume Grating Coupler-Based Optical Interconnect Technologies for
Polylithic Gigascale Integration

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Presented to
The Academic Faculty

by

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Volume Grating Coupler-Based Optical Interconnect Technologies for
Polyolithic Gigascale Integration

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Dedication

To my loving family

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Table of Contents

Dedication	iii
Acknowledgements	iv
List of Tables	ix
List of Figures	xi
List of Symbols	xxvi
List of Abbreviations	xxxvii
Summary	x1
Chapter 1: Polyolithic Integration of Electrical and Optical Interconnect Technologies	
1.1 Introduction	1
1.2 Monolithic Integration	2
1.3 Hybrid Integration	6
1.4 Optical Transceiver Fiber-to-the-Chip Technologies	14
1.5 Polyolithic Integration: Gigascale Fiber-to-the-Chip Communication	23
1.6 Optical Interconnect Technologies for Gigascale Polyolithic Integration	36
1.7 References	38
Chapter 2: Electrical and Optical Clock Distribution Networks for High-Performance Microprocessors	
2.1 Introduction	43
2.2 Characterization of Clock Distribution Networks	45
2.3 Performance Limitations of Conventional Electrical Clock Distribution Networks	47
2.4 2002 ITRS 32-nm (2013) Technology Generation: Initial Technology Generation Meriting Alternate Global Clocking Methodology	53

Table of Contents (Cont'd)

2.5 General Properties of Optical Clock Distribution Networks	54
2.6 Optical Clock Distribution Networks Reported in the Literature	59
2.7 Strengths and Weaknesses of Optical Clock Distribution	65
2.8 Summary	73
2.9 References	75
Chapter 3: Electrical and Optical Time-of-Flight Interconnect Partitions	
3.1 Introduction	86
3.2 Hybrid Electrical/Optical System Overview	90
3.3 Electrical-to-TOF Interconnect Partitions	92
3.4 TOF Interconnect Routing Area	94
3.5 Summary	102
3.6 References	103
Chapter 4: Design, Fabrication, and Test of Volume Grating Couplers	
4.1 Introduction	105
4.2 Available Methods of Coupling	106
4.3 Grating Diffraction Theory	116
4.4 Design of Volume Grating Couplers	125
4.5 Fabrication of Volume Grating Couplers	136
4.6 Testing of Volume Grating Couplers	143
4.7 Summary	149
4.8 References	150

Table of Contents (Cont'd)

Chapter 5: Avatrel 2190P Optical Interconnect Structures	
5.1 Introduction	154
5.2 Avatrel 2190P Film Properties	155
5.3 Fabrication, Test of Avatrel 2190P Waveguides	156
5.4 Design, Fabrication, and Test of Avatrel 2190P Multimode Interference Power Splitters and Waveguide Tapers	163
5.5 Summary	181
5.6 References	182
Chapter 6: Wafer-Level Fabrication of Compatible Electrical, Optical I/O	
6.1 Introduction	184
6.2 Overview of Wafer-Level Batch Package-Embedded Optical Interconnection	185
6.3 Fabrication and Test of Air-Clad Optical Waveguides	196
6.4 Fabrication and Test of Wafer-Level Batch Package Optical I/O: Index-Defined Waveguides and Volume Grating Couplers	204
6.5 Summary	221
6.6 References	222
Chapter 7: Grating-to-Grating Coupling for Board-to-Chip Optical I/O	
7.1 Introduction	224
7.2 Grating-to-Grating Substrate Fabrication and Characterization	225
7.3 Grating-to-Grating Coupling Efficiency Measurement	247
7.4 Summary	275

Table of Contents (Cont'd)

Chapter 8: Conclusions and Future Work	
8.1 Conclusions and Future Work	276
8.2 References	284
Vita	285

List of Tables

Table 1.1	Summary of fiber-to-the-chip transceiver technologies.	22
Table 1.2	2002 ITRS projections for high-performance microprocessors.	28
Table 1.3	Electrical I/O, interconnect layer requirements vs. substrate-level electrical interconnect bit-rate, technology generation for 20 Tb/s/direction gigascale fiber-to-the-chip communication.	35
Table 2.1	Summary of high-performance electrical clock distribution networks reported in the literature.	50
Table 2.2	Percentage of test period consumed by short-term jitter for reported microprocessors.	50
Table 2.3	Projections for short-term jitter and skew vs. technology generation.	53
Table 2.4	Summary of inter-board through intra-chip optical clock distribution networks.	65
Table 3.1	Prior estimations of electrical-to-optical partition lengths.	87
Table 3.2	Rent's parameters and gate count of megacells scaled to 45 nm technology. k is Rent's parameter, N_{gates} is the number of gates, and p is Rent's Exponent.	94
Table 3.3	Waveguide materials. PNB = Polynorbornene, MSQ = Methylsilsequioxane, TMSNB = Tri-methyl substituted norbornene, and NA = Not Applicable.	95
Table 3.4	Partition length, clock frequency vs. waveguide technology and optical wavelength. C = Core, UC = Upper Clad, LC = Lower Clad, and NA = Not Applicable.	95
Table 4.1	Diffraction properties of supported modes for grating-in-the-waveguide volume grating coupler.	134
Table 4.2	Summary of grating design parameters.	141
Table 4.3	Summary of grating performance parameters.	141
Table 4.4	Summary of grating fabrication parameters.	142

List of Tables (Cont'd)

Table 5.1	Avatrel 2190P film properties.	156
Table 5.2	Cauchy parameters for 2.5 μm thick Avatrel 2190P dielectric film on Si.	156
Table 5.3	Summary of loss measurements performed on 5 μm wide/25 μm pitch raised-strip Avatrel 2190P waveguides.	161
Table 5.4	Optimal MMI device length as a function of MMI device width.	174
Table 5.5	Variations in optimal MMI device length with optical wavelength.	174
Table 6.1	Board-level grating design summary .	190
Table 6.2	Optical system properties.	190
Table 6.3	Summary of loss measurements performed on 5 μm wide/25 μm pitch passivated raised-strip Avatrel 2190P waveguides.	201
Table 6.4	Summary of loss measurements performed on 100 μm wide/325 μm pitch unpassivated index-defined Avatrel 2190P waveguides.	210
Table 7.1	Summary of Avatrel/Omnidex adhesion experiments.	227
Table 7.2	Summary of grating coupling coefficient, length for bottom, top grating-to-grating substrate gratings.	244
Table 7.3	Summary of propagation loss metrics for Avatrel waveguide segments leading into diffraction gratings located on bottom, top grating-to-grating substrate gratings.	245
Table 7.4	Summary of propagation loss metrics for Avatrel waveguides situated between diffraction grating channels located on bottom grating-to-grating substrate.	245
Table 7.5	Summary of grating-to-grating coupling efficiency measurements.	264

List of Figures

Figure 1.1	Monolithic integration of GaAs lasers on silicon through graded $\text{Ge}_x\text{Si}_{1-x}$ layers (M.E. Groenert, V.K. Yang, C.W. Leitz, M.T. Currie, A.J. Pitera, Harry Lee, R.J. Ram and E.A. Fitzgerald, Massachusetts Institute of Technology).	4
Figure 1.2	Monolithic integration of Er-doped silicon LEDs with CMOS [1.7].	6
Figure 1.3	Polyimide bonding process: a) Polyimide bonding of GaAs and silicon wafers; b) Substrate and selective epitaxial etch; c) Completed optoelectronic devices on silicon CMOS [1.10].	8
Figure 1.4	Flip-chip bonding of optoelectronic device using indium bump bonding: a) Contact definition and mesa etch on GaAs substrate; b) Application of epoxy, device bonding; c) GaAs substrate removal and anti-reflection (AR) coating (David Miller, Stanford University).	10
Figure 1.5	Hybrid bonding of III-V VCSEL to silicon CMOS [1.12].	11
Figure 1.6	Epitaxial lift-off technique using polyimide transfer diaphragm [1.14]: a) Epitaxial layers atop III-V substrate; b) Mesa etch to define devices; c) Contact metallization; d) Encapsulation in transfer wax; e) Epitaxial lift-off through selective etch; f) Van der Waals bonding of device array to polyimide diaphragm; g) Wax removal and alignment of devices to host substrate.	13
Figure 1.7	Optobus transceiver module [1.19].	15
Figure 1.8	Exploded view of OETC optoelectronic package [1.20]. An aluminum heat sink (not shown) is attached to the heat spreader.	17
Figure 1.9	Fiber array block (upper right of figure) situated atop a silicon base plate and aligned to a VCSEL transmitter array. SEL = surface emitting laser, and PD = (monitor) photodetector. The FAB is contained within the OSA portion of Fig. 1.8 [1.20].	18
Figure 1.10	a) POLO-1 module [1.21]; b) POLO-2 module [1.23]. Both depictions are shown with the exterior housing removed.	19
Figure 1.11	Components of the POLO-2 module [1.22].	20

List of Figures (Cont'd)

Figure 1.12	a) PONI module [1.23]; b) Heat sink and thermocouple assembly for PONI module [1.24]. POSA = parallel optical sub-assembly.	21
Figure 1.13	Gigascale fiber-to-the-chip data communication using polyolithic integration.	25
Figure 1.14	Cost vs. complexity tradeoff in high-performance (1 Tb/s) fiber-to-the-chip interconnection [1.29].	29
Figure 1.15	Schematic of substrate-level electrical interconnect traces illustrating via radius, r_{via} , trace spacing, d_{trace} , trace width, W_{trace} , and via/I/O pitch, $P_{I/O}$. The number of traces is $N_{trace} = 2$.	32
Figure 1.16	Electrical traces routed on a single interconnect layer. The number of traces between I/O, N_{trace} , dictates the number of columns reached per layer. For the I/O array depicted, the number of traces is $N_{trace} = 1$ and the total number of required layers is $N_{layer} = 2$.	32
Figure 1.17	Gigascale inter-chip/intra-chip optical clock distribution using polyolithic integration.	36
Figure 2.1	Percentage of clock period consumed by global skew vs. clock frequency for microprocessors of Table I. Linear fit to data is shown.	51
Figure 2.2	Percentage of test period consumed by short-term jitter vs. test frequency for microprocessors of Table 2.2. Linear fit to data is shown.	51
Figure 2.3	Focused free-space optical clock distribution configuration [2.36].	56
Figure 2.4	Substrate-mode guided-wave optical clock distribution configuration [2.37].	57
Figure 2.5	Optical clock distribution using integrated optical waveguides.	58
Figure 2.6	Preferential-order volume focusing grating coupler [2.58, 2.59].	68
Figure 3.1	Chip-level optical data interconnection.	91
Figure 3.2	Optical crosstalk coupling coefficient κ vs. separation distance d_{wg} for SiO ₂ /Air/MSQ waveguides.	97

List of Figures (Cont'd)

Figure 3.3	Normalized routing area vs. partition length for optical waveguide and electrical interconnect technologies.	99
Figure 4.1	Endfire (butt) coupling of optical power into optical component [4.4].	106
Figure 4.2	Prism coupling into optical waveguide.	107
Figure 4.3	Input coupling from a laser array using a reflective coupler.	108
Figure 4.4	Non-focusing preferential volume grating (left) and non-focusing non-preferential surface-relief grating (right). Λ is the grating period and ϕ is the grating slant angle.	109
Figure 4.5	Preferential coupling in diffractive gratings: a) Surface-relief grating using a dielectric reflective layer; b) Surface-relief grating using a double grating; c) Surface-relief grating with a blazed grating profile; d) Volume diffraction grating with a slant in the lines of refractive index modulation.	110
Figure 4.6	a) Surface-relief focusing grating; b) Volume focusing grating. Focusing to a line is achieved by decreasing the grating period along the x direction and leaving the grating fringes unchanged in the y direction. Focusing to a spot is achieved in either grating by introducing a curvature in the grating fringes along the y-direction (as shown in b).	111
Figure 4.7	Variable coupling rate diffractive gratings: a) Surface-relief grating using a variable grating height; b) Surface-relief grating using a variable fill factor; c) Surface-relief grating above a waveguide with a tapered thickness; d) Volume diffraction grating with a chirp in the slant angle along the length of the grating.	112
Figure 4.8	Volume diffraction grating coupler configurations: a) Grating-on-the-waveguide; b) Grating-in-the-waveguide.	114
Figure 4.9	Inhomogeneous plane waves (space harmonics) propagating inside diffraction grating according to vector Floquet condition [4.9]. The phase front of each space harmonic is perpendicular to the corresponding Floquet wavevector. θ' is the angle of incidence.	119

List of Figures (Cont'd)

Figure 4.10	Preferential coupling of optical power using slanted grating fringes: a) Preferential coupling into cover region; b) Preferential coupling into substrate region.	126
Figure 4.11	<i>k-space</i> diagram for grating-in-the-waveguide configuration.	127
Figure 4.12	Overlap of normalized intensity profiles of non-focusing volume coupler and Gaussian input beam. The non-focusing coupler with constant slant angle (and hence coupling coefficient $\alpha_{v=0}$) has an exponential out-coupled intensity.	136
Figure 4.13	Interferometric recording configuration for defining volume grating couplers.	137
Figure 4.14	Interferometric recording of volume grating: a) Plane-wave interference within photopolymer sample; b) Angles of incidence of two recording beams and propagation through prism coupler.	138
Figure 4.15	Qualitative assessment of grating uniformity using a 488 nm test beam. The sample initially exhibits no substrate-mode coupling (left). Upon rotation, the sample exhibits substrate-mode coupling over all areas corresponding to a functional grating (right).	144
Figure 4.16	Rotation stage measurement configuration for quantification of Bragg angle, input coupling efficiency, and uniformity of volume grating couplers.	144
Figure 4.17	Bragg angle, input coupling efficiency measurements of volume grating coupler. A peak input coupling efficiency of 76.25 % is recorded for this sample at an incident (Bragg) angle of 0.5°.	145
Figure 4.18	Uniformity of Bragg angle, input coupling efficiency as measured at different locations on the grating substrate. Peak input coupling efficiency varies from 40-59 % as recorded laterally across the grating/waveguide interface. No significant deviations in Bragg angle, however, are observed.	146

List of Figures (Cont'd)

- Figure 4.19 Image capture test station. A fiber-coupled laser diode feeds the sample under test, which is mounted atop a waveguide mount. The fiber position is optimized through un-aided visual inspection and through microscope-aided inspection. An optional polarization controller can be included to perform polarization-dependent coupling coefficient measurements. This setup is also used to measure propagation loss in optical waveguides, as discussed in Chapter 5. 148
- Figure 4.20 Out-coupled intensity of volume diffraction grating. A linear least-squares fit to the data indicates TE and TM coupling coefficients α_{TE} and $\alpha_{TM} = 7 \text{ cm}^{-1}$ and 2 cm^{-1} , respectively. 149
- Figure 5.1 Robust linear least square fit of propagation loss measurement data for waveguide 1 of Table 5.3. An exposure time of 50 ms was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -3.35 \text{ dB/cm}$. 161
- Figure 5.2 Robust linear least square fit of propagation loss measurement data for waveguide 2 of Table 5.3. An exposure time of 50 ms was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -5.53 \text{ dB/cm}$. 162
- Figure 5.3 Robust linear least square fit of propagation loss measurement data for waveguide 3 of Table 5.3. An exposure time of 50 ms was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -6.76 \text{ dB/cm}$. 163
- Figure 5.4 Three common power splitter structures: a) Y-junction power splitter; b) 3dB directional coupler; c) Multimode interference power splitter. 165

List of Figures (Cont'd)

- Figure 5.5 Linewidth/spacing resolution in Avatrel 2190P: a) 1 x 2 MMI device with 2/4 μm width/pitch output waveguides; b) 1 x 2 MMI device with 2/5 μm width/pitch output waveguides; c) 1 x 4 MMI device with 2/6 μm width/pitch output waveguides. Each device is 0.9 μm thick and was constructed from a 25%-weight solution of Avatrel 2190P. A clear reduction in the rounded-nature of the device edges is noted with increasing pitch from left to right. 168
- Figure 5.6 First-run 1 x 2 MMI coupler with 5/10 μm width/pitch output waveguides: a) Device; b) CCD output; c) Intensity plot of CCD output (beam uniformity); d) Contour plot of CCD output (modal profile). The output uniformity depicted in c) is misleading due to the saturation of the image. 169
- Figure 5.7 First-run 1 x 4 MMI coupler with 5/10 μm width/pitch output waveguides: a) Device; b) CCD output; c) Intensity plot of CCD output (beam uniformity); d) Contour plot of CCD output (modal profile). Note the presence of a multi-mode output in each of the output waveguides, suggesting the excitation of the symmetric, third-order lateral mode within the waveguide feeding the MMI region. 170
- Figure 5.8 First-run 1 x 16 MMI coupler with 5/10 μm width/pitch output waveguides: a) Device; b) CCD output; c) Intensity plot of CCD output (beam uniformity); d) Contour plot of CCD output (modal profile). Note: The degree of uniformity between neighboring outputs depicted in c) is misleading due to image saturation. The output is skewed additionally due to the slanted cleave of the output waveguides, as seen in a). 171
- Figure 5.9 First-run 1 x 32 MMI coupler with 4/9 μm width/pitch output waveguides: a) Device; b) CCD output; c) Intensity plot of CCD output (beam uniformity); d) Contour plot of CCD output (modal profile). Note: The degree of uniformity between certain neighboring outputs depicted in c) is misleading due to image saturation. The output is skewed additionally due to the slanted cleave of the output waveguides, as seen in a). 172
- Figure 5.10 Cross-cut of MMI region obtained from Wycko optical profilometer. Note: The height scale given in Fig. 5.13 is un-calibrated. 175

List of Figures (Cont'd)

Figure 5.11	Image capture of 1 x 4 MMI output. The width of the MMI region is 26.3 μm and the length is 421.7 μm .	177
Figure 5.12	Quantification of device output depicted in Fig. 5.14: a) Intensity plot of CCD output (beam uniformity); b) Contour plot of CCD output (modal profile). The DNR is 27.1 dB and output uniformity is 0.3-0.6 dB for 3x3-11x11 pixel matrices, respectively.	177
Figure 5.13	End view of $\sim 1\mu\text{m}$ thick Avatrel 2190P channel waveguides fabricated from 25% weight solids solution. A clear slope in channel sidewalls is visible.	178
Figure 5.14	End view of $\sim 1.3\mu\text{m}$ thick Avatrel 2190P channel waveguides. A slight slope in channel sidewalls is visible.	178
Figure 5.15	10:2 μm waveguide taper: a) Wycko optical profilometer measurement; b) CCD image of waveguide output; c) Intensity plot of CCD output (beam uniformity); d) Contour plot of CCD output (modal profile).	180
Figure 6.1	Wafer-level batch package with optical I/O. Bulk silicon detectors are incorporated to provide optical-to-electrical conversion of optical signals. Labeled are a) detector, b) volume gratings, c) metallization, d) passivation, e) waveguide core, and f) reflection mirror.	186
Figure 6.2	Reflection mirror fabricated in Omnidex photopolymer material using plasma etching.	187
Figure 6.3	Volume focusing grating coupler.	189
Figure 6.4	Ray trace of focal plane under wavelength and spatial variations. From top to bottom: 840, 850, and 860 nm, respectively, over a 20 μm vertical range of spatial deviations. The longitudinal optical beam width, $\Delta x_{\Delta\lambda}$, is labeled.	191

List of Figures (Cont'd)

- Figure 6.5 Finite difference time domain (FDTD) simulations of a 20 μm bend radius for optical waveguides with core refractive index $n_{\text{core}} = 1.54$ and cladding refractive index of a) 1 (i.e. air-cladding) for $\Delta n = 0.54$ (resulting in a -1.2 dB loss) and b) 1.51 for $\Delta n = 0.03$ (resulting in the loss of all optical power). The optical wavelength and waveguide width are $\lambda_o = 1.5 \mu\text{m}$ and $w_{\text{wg}} = 1 \mu\text{m}$ respectively. The y-component of the TE-polarized electric field is shown. Note the difference in confinement for each technology within the waveguide region at the start of the right-angle bend due to the difference in Δn . 193
- Figure 6.6 Coupling coefficient vs. separation distance between two parallel buried channel waveguides implemented in a) nano air-gap [6.11] ($n_{\text{core}} = 1.4$, $n_{\text{clad}} = 1.3$) and b) bulk polynorborene [6.9] ($n_{\text{core}} = 1.54$, $n_{\text{clad}} = 1.51$) material systems. Each waveguide has $w_{\text{wg}} = 2 \mu\text{m}$ and $t_{\text{wg}} = 1 \mu\text{m}$. The optical wavelength $\lambda_o = 0.85 \mu\text{m}$. 193
- Figure 6.7 FDTD simulations of a) tapered reflection mirror with $\Delta n = 0.51$; b) Ag metallization on mirror surface (-0.13 dB loss); c) no metallization (-0.74 dB loss). The optical wavelength and waveguide thickness are $1.5 \mu\text{m}$ and $6 \mu\text{m}$ respectively. The length of the tapered mirror extends over a $10 \mu\text{m}$ opening filled with a low- κ dielectric. The y-component of the TE-polarized electric field is shown. 195
- Figure 6.8 High-volume test of optical interconnect-enable wafer-level package with optoelectronic probe card. 196
- Figure 6.9 Fabrication sequence for optical waveguides in embedded air-cladding regions. 197
- Figure 6.10 SEM cross-sectional view of 1/5/25 μm thick/width/pitch optical waveguides within an encapsulated air cavity. The encapsulated air-cladding region is $\sim 15 \mu\text{m}$ thick, formed from a viscous solution of Unity 200P. 200
- Figure 6.11 SEM cross-sectional view of 5/5/25 μm thick/width/pitch optical waveguides within an encapsulated air cavity. The encapsulated air-cladding region is $\sim 8 \mu\text{m}$ thick. 200

List of Figures (Cont'd)

Figure 6.12	Robust bisquare linear least square fit of loss measurement data for waveguide 1 of Table 6.3. An exposure time of 50 ms was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -2.34$ dB/cm. The plot of residual error reveals that the variance is constant along the chosen fit range.	202
Figure 6.13	Robust linear least square fit of loss measurement data for waveguide 2 of Table 6.3. An exposure time of 50 ms was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -4.38$ dB/cm. The plot of residual error reveals that the variance is relatively constant along the chosen fit range.	203
Figure 6.14	Robust linear least square fit of loss measurement data for waveguide 3 of Table 6.3. An exposure time of 50 ms was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -6.63$ dB/cm. The plot of residual error reveals that the variance is constant along the chosen fit range.	204
Figure 6.15	Two-material grating-in-the-waveguide optical waveguide interconnect.	205
Figure 6.16	Avatrel/Omnidex waveguide/grating (WG/G) interface in presence of wet development step.	206
Figure 6.17	Cross-sectional schematic of index-defined channel waveguide.	209
Figure 6.18	Top-view through Olympus digital camera of Avatrel 2190P index-defined channel waveguides using a 2x Mitutoyo objective. Waveguide regions are clearly visible. A reflection from the fiber input is visible on the left. The length of the depicted segment is ~ 8 mm, and the total waveguide length is ~ 2.5 cm.	209
Figure 6.19	View of out-coupled power looking longitudinally into end of excited index-defined waveguide under a) low-power excitation and b) high-power excitation. All propagation loss measurement data are recorded under high-power excitation conditions.	210
Figure 6.20	Robust linear least square fit of loss measurement data for waveguide 1 of Table 6.4. An exposure time of 5s was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -5.39$ dB/cm. The plot of residual error reveals that the variance is constant along the chosen fit range.	211

List of Figures (Cont'd)

Figure 6.21	Robust linear least square fit of loss measurement data for waveguide 2 of Table 6.4. An exposure time of 5s was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -5.55$ dB/cm. The plot of residual error reveals that the variance is constant along the chosen fit range.	212
Figure 6.22	Robust linear least square fit of loss measurement data for waveguide 3 of Table 6.4. An exposure time of 5s was used to record the image. The slope of the fit corresponds to a loss of $\alpha_{wg} = -8.78$ dB/cm. The plot of residual error reveals that the variance is constant along the chosen fit range.	213
Figure 6.23	Robust linear least square fit of loss measurement data for RIE-patterned Omnidex waveguide channel. The slope of the fit corresponds to a loss of $\alpha_{wg} = -86.75$ dB/cm. The plot of residual error reveals that the variance is constant along the chosen fit range.	214
Figure 6.24	Non-planar topography of cured Omnidex film.	215
Figure 6.25	Transmitted intensity vs. angle of incidence (i.e., input coupling efficiency) measurements for slab volume diffraction grating #1 before and after encapsulation in Avatrel 2190P.	216
Figure 6.26	Transmitted intensity vs. angle of incidence (i.e., input coupling efficiency) measurements for slab volume diffraction grating #2 before and after encapsulation in Avatrel 2190P.	216
Figure 6.27	Fabrication sequence corresponding to optical layer of wafer-level batch package with optical I/O.	217
Figure 6.28	Top-down view of optical layer of wafer-level package following encapsulation in Avatrel. Linked Ti/Au I/O pads and individual grating channels are clearly visible.	219
Figure 6.29	Out-coupled intensity from grating channel of sample depicted in Figure 6.28. Note the lack of reflected/scattered power at the Avatrel/Omnidex interface. A coupling coefficient of 10.4 mm^{-1} is fit to the measured data using robust linear least-squares regression.	220

List of Figures (Cont'd)

Figure 7.1	Grating-to-grating coupling.	225
Figure 7.2	(left) Sample #3 from Table 7.1; (right) Sample #6 from Table 7.1. Labeled are a) Air-cladding between neighboring waveguides; b) Avatrel channel waveguide without grating photopolymer channel; c) Avatrel channel waveguide with grating photopolymer channel.	229
Figure 7.3	Bragg angle, input coupling measurements for grating sample fabricated for evaluating impact of glass + Avatrel passivation on grating performance. A peak input coupling efficiency of 52.6% is observed at 0.6° .	230
Figure 7.4	Optical profilometer scan of Avatrel-encapsulated volume grating channels. The nature of Avatrel is such that a non-planar topology results when the material is spun onto a substrate with existing features. The thickness of the interconnect increases in the grating region by the thickness of the applied Avatrel film.	231
Figure 7.5	Contact profilometer scan of Avatrel-encapsulated volume grating channels. The total film thickness increases within the grating region by that of the Avatrel layer. A curved surface profile is added to the polymer/air interface above each grating. The dashed-inset represents an approximation to the Omnidex grating channel surface profile.	232
Figure 7.6	Location of Bragg angle, input coupling measurements of slab diffraction gratings that will serve as the bottom and top substrates for grating-to-grating coupling measurements.	233
Figure 7.7	Bragg angle, input coupling measurements of slab diffraction grating prior to channel patterning and encapsulation in SiO_2 and Avatrel that will serve as the top-substrate. A peak input coupling efficiency of 59% is observed around 0.25° and 0.55° .	234
Figure 7.8	Micrograph of two-material grating-in-the-waveguide optical interconnects composed of Avatrel waveguide regions and Omnidex grating coupler regions.	236
Figure 7.9	a) Writing scribe line into patterned grating substrate; b) Mounting substrate, breaking cleave line.	237

List of Figures (Cont'd)

Figure 7.10	Reflected optical power from a poorly-cleaved waveguide facet. The image was captured using the Q-Color 3 digital camera using an extended exposure time.	238
Figure 7.11	Cleaved edge using procedure described in Fig. 7.8.	238
Figure 7.12	Location of Bragg angle, input coupling measurements of patterned top-substrate.	240
Figure 7.13:	Bragg angle, input coupling measurements of patterned top substrate. A collimated HeNe test beam is used to excited the substrate during measurement. The nature of the transmitted intensity profile matches that exhibited in Fig. 7.6 in both overall form and in the specific location of the the maximum dip in transmitted intensity, which occurs around 0.25° .	241
Figure 7.14:	Top-view micrograph of bottom-substrate depicting grating/waveguide channels 1-8 and waveguide channels 1-7. Black magic marker applied to the bottom of the substrate prior to imaging contributes to a non-uniform background in the image.	242
Figure 7.15:	Robust bisquare linear least square fit to out-coupled intensity data for grating #4 on bottom-substrate resulting in a coupling coefficient $\alpha_g = 1.77 \text{ mm}^{-1}$.	243
Figure 7.16:	Robust bisquare linear least square fit to scattered intensity data for Avatrel waveguide leading into grating #4 on bottom substrate resulting in a propagation loss coefficient $\alpha_{wg} = -6.89 \text{ dB/cm}$.	243
Figure 7.17:	Robust bisquare linear least square fit to scattered intensity data for stand-alone Avatrel waveguide #4 on bottom substrate, resulting in a propagation loss coefficient $\alpha_{wg} = -6.78 \text{ dB/cm}$.	244
Figure 7.18:	a) View through Cohu CCD, Optem microscope tube, and 20x Mitutoyo objective during characterization of a grating channel; b) Schematic of view depicted in a).	246

List of Figures (Cont'd)

- Figure 7.19: Comparison of image-capture and detector-scan methods of characterizing coupling coefficient data for a volume grating. Both methods result in a coupling coefficient of 2.5 mm^{-1} . The data corresponding to the image-capture method was acquired using a 1.6 ms exposure time and an applied laser current of 50 mA. The data corresponding to the detector-scan method was acquired using an applied laser current of 70 mA. Both sets of intensity data are normalized for comparison purposes. 247
- Figure 7.20: Grating-to-grating measurement setup. The top-substrate is suspended above the bottom-substrate during measurement using the rotation arm such that the relative lateral, longitudinal, and vertical position of the top-substrate is controlled with micron resolution. The relative roll and pitch of the top substrate is controlled to within 0.02° , while the relative yaw is minimized by aligning waveguides on both substrates through visual inspection using the translatable microscope. 250
- Figure 7.21: Image of top, bottom-substrates taken during pitch initialization. The relative angular position of the top substrate is initialized to $\sim 0^\circ$. 251
- Figure 7.22: Images of top, bottom-substrate during roll initialization: a) A relative roll angle of 1.25° ; b) A relative roll angle of 0° after initialization. 252
- Figure 7.23: View of light coming from bottom-substrate waveguide/grating channel under excitation and corresponding reflection from top substrate. The background light from the input fiber is minimized due to the removal of the fiber cladding modes by winding the input fiber present prior to the fiber chuck around a small circular object. 254
- Figure 7.24: View of grating-to-grating optical coupling in presence of unfocused background light from bottom-substrate waveguide/grating channel and corresponding reflection. The top-substrate waveguide/grating channel is positioned laterally outside of the range for grating-to-grating coupling. 255

List of Figures (Cont'd)

Figure 7.25:	View of grating-to-grating optical coupling in presence of unfocused background light from bottom-substrate waveguide/grating channel and corresponding reflection. The top-substrate is shifted laterally such that grating-to-grating coupling occurs, as indicated by the light emitted from the waveguide region.	256
Figure 7.26:	Grating-to-grating coupling vs. relative longitudinal position of top-substrate: a) Initial reference location; b) +300 μm ; c) + 500 μm ; d) + 900 μm ; e) +1660 μm .	259
Figure 7.27:	Grating-to-grating coupling vs. relative vertical placement of top-substrate: a) Initial reference location; b) + 1000 μm ; c) + 2000 μm ; d) +3000 μm ; e) +4000 μm . Note the gradual reduction in the unfocused background light as the height of the top substrate increases above the bottom-substrate.	262
Figure 7.28:	Top-down view of bottom-substrate diffraction grating as seen through objective/detector configuration used to monitor the relative change in transmitted intensity.	263
Figure 7.29:	Measurements of Bragg angle, input coupling efficiency for un-patterned, un-passivated top-substrate referenced in Table 7.5. Measurement locations referenced in the figure correspond to the locations depicted in Fig. 7.5.	265
Figure 7.30:	Transmitted intensity vs. angle of incidence measurement data corresponding to a patterned bottom-substrate with an encapsulated grating coupled optically to a patterned top substrate with an encapsulated grating (case #1 of Table 7.5). The peak grating-to-grating coupling efficiency is 12%.	266
Figure 7.31:	Transmitted intensity vs. angle of incidence measurement data corresponding to a patterned bottom-substrate with an encapsulated grating coupled optically to an un-patterned top substrate with an un-encapsulated grating (case #2 of Table 7.5). Each of the two lines corresponds to a different test location on the top-substrate. The peak grating-to-grating coupling efficiency is 19.8%.	267

List of Figures (Cont'd)

- Figure 7.32: Transmitted intensity vs. angle of incidence measurement data corresponding to a patterned bottom-substrate with an encapsulated grating coupled optically to an un-patterned top substrate with an encapsulated grating (case #3 of Table 7.5). The peak grating-to-grating coupling efficiency is 26%. 269
- Figure 7.33: Transmitted intensity vs. angle of incidence measurement corresponding to an un-patterned bottom-substrate with an un-encapsulated grating coupled optically to a patterned top substrate with an encapsulated grating (case #4 of Table 7.5). The lack of full coverage of the optical power diffracted from the bottom substrate by the top-substrate contributes to the reduced magnitude of the dip in transmitted intensity and the discrete nature of the data points. The peak grating-to-grating coupling efficiency in the presence of poor coverage is 3%. 270
- Figure 7.34: Transmitted intensity vs. angle of incidence measurement data corresponding to an un-patterned bottom substrate with an un-encapsulated grating coupled optically to an un-patterned top substrate with an un-encapsulated grating (case #5 of Table 7.5). 271
- Figure 7.35: Transmitted intensity vs. angle of incidence measurement data corresponding to an un-patterned bottom substrate with an un-encapsulated grating coupled optically to an un-patterned top substrate with an encapsulated grating (case #6 of Table 7.5). 272
- Figure 7.36: Transmitted intensity vs. angle of incidence measurement data corresponding to an un-patterned bottom substrate with an un-encapsulated grating coupled optically to an un-patterned top substrate with an encapsulated grating (case #6 of Table 7.5). 273

List of Symbols

A_{chip}	Chip area
P_{chip}	Chip power dissipation
$P_{density}$	Power density
F_{clock}	Clock frequency
N_{tx}	Transistor count
$N_{I/O}$	ITRS-projected microprocessor I/O count
$C_{I/O}$	Cost per I/O
$d_{I/O}$	Via, I/O pad pitch
W_{trace}	Substrate electrical interconnect trace width
d_{trace}	Substrate electrical interconnect edge-to-edge trace spacing
$N_{I/O}'$	Revised total I/O count (ITRS projected I/O count + N_{GF2C})
N_{GF2C}	Number of I/O required for gigascale fiber-to-the-chip communication
N_{layers}	Number of substrate-level electrical interconnect trace layers (based on ITRS projections)
N_{layers}'	Revised number of substrate-level electrical interconnect trace layers (based ITRS projections + Gigascale fiber-to-the-chip considerations)
N_{ch}	Number of multiplexed electrical channels per optical I/O
$B_{Elec-Sub}$	Substrate-level electrical interconnect bit-rate
$N_{I/O,Elec-Opt}$	Number of signal I/O connecting microprocessor and optoelectronic die
r_{via}	Escape via radius
L_{trace}	Substrate electrical interconnect trace length
K_o	Electrical interconnect bandwidth constant

List of Symbols (Cont'd)

N_{trace}	Number of allowed escape traces between escape vias
TG	ITRS technology generation
V_{dd}	Supply voltage
L	CMOS transistor channel length
σ_{skew}	% local clock period consumed by skew
σ_{jitter}	% local clock period consumed by jitter
W_{opt}	Optimum on-chip interconnect width
W	On-chip interconnect width
τ	On-chip interconnect delay
c_o	Speed of light in a vacuum
ξ	Constant describing on-chip interconnect geometry
ρ	Metal resistivity
ε_o	Average relative permittivity
R_o	Output resistance of a minimum size repeater
C_o	Input capacitance of a minimum size repeater
$l_{elec-opt}$	Electrical-to-optical interconnect partition length
ε_r	Relative dielectric constant
N_{eff}	Effective refractive index of fundamental waveguide mode
D_{chip}	Chip edge length
$l_{elec-ext}$	Partition length between chip-level electrical interconnect and board-level electrical interconnect
L_t	Total length of all interconnects longer than partition length

List of Symbols (Cont'd)

A_{opt}	Routing area of optical waveguide partition
d_{opt}	Optical waveguide pitch
A_{ext}	Routing area of electrical exterconnect partition
d_{ext}	Electrical exterconnect pitch
e_{part}	Routing efficiency of optical waveguide or electrical exterconnect partition
k	Rent's parameter
N_{gates}	Number of logic gates
p	Rent's exponent
λ_o	Free-space optical wavelength
F_{max}	Maximum on-chip global clock frequency
κ	Crosstalk coupling coefficient
d_{wg}	Edge-to-edge optical waveguide separation distance
K	Optical crosstalk constant
x	Propagation/longitudinal distance/direction
P_0	Initial power launched into source waveguide
P_{source}	Optical power in source waveguide
P_{victim}	Optical power in victim waveguide
L_{couple}	Crosstalk coupling distance
$n_{lower-clad}$	Lower-cladding refractive index
$n_{upper-clad}$	Upper-cladding refractive index
n_{core}	Core refractive index
ϵ	Relative permittivity

List of Symbols (Cont'd)

n_p	Prism refractive index
θ_V	Angle with respect to the normal of the lower prism-air interface
ν	Mode reference index
k_o	Freespace wavevector
β_ν	Propagation constant of ν^{th} mode
n_{wg}	Waveguide film refractive index
$\theta_{zz,\nu}$	Zig-zag angle of the ν^{th} guided-mode
$W_{half}(x)$	Beam half-width
W_{ap}	Aperture width
$W_{coupler}$	Volume grating coupler width
$L_{coupler}$	Volume grating coupler length
Λ	Grating period
λ_r	Holographic read wavelength
ϕ	Grating slant angle
$E_y(x, z)$	Electric field inside diffraction grating
ε_1	Amplitude of sinusoidal relative permittivity
K_x	x -component of grating vector
K_z	z -component of the grating vector
\bar{K}	Grating vector
$S_i(z)$	Amplitude of the i^{th} space-harmonic of the Fourier expansion of $E_y(x, z)$ along the direction of periodicity
\bar{r}	Unit vector

List of Symbols (Cont'd)

$\bar{\sigma}_i$	Floquet wavevector of i^{th} space harmonic
$\bar{\sigma}_{ix}$	x - component of Floquet wavevector of i^{th} space harmonic
$\bar{\sigma}_{iz}$	z - component of Floquet wavevector of i^{th} space harmonic
i	Space harmonic (diffracted order) reference index
\bar{k}_2	Wavevector of 0^{th} diffracted order in grating region
k_{2x}	x -component of 0^{th} order wavevector
k_{2z}	z -component of 0^{th} order wavevector
θ	Angle of refraction of incident plane wave within the grating region
θ_i	Angle of diffraction of space harmonic within grating region
θ_i'	Angle of diffraction of space harmonic into backward diffraction region
θ_i''	Angle of diffraction of space harmonic into forward diffraction region
θ'	Angle of incidence of plane wave incident on grating
m	Bragg condition index
A	Space harmonic coefficient matrix
S	Space harmonic matrix
\dot{S}	Space harmonic derivative matrix
a	Space harmonic coefficient matrix constant
b_i	Space harmonic coefficient matrix factor of i^{th} diffracted order
c_i	Space harmonic coefficient matrix factor of i^{th} diffracted order
l	Space harmonic amplitude reference index

List of Symbols (Cont'd)

C_m	Space harmonic constants determined from electromagnetic boundary conditions
$w_{l,im}$	Element of space harmonic component eigenvector found from coefficient matrix
λ_m	Eigenvalue of space harmonic component eigenvector found from coefficient matrix
N	Number of space harmonics retained for computation of coefficients
ϵ_I	Relative permittivity of forward diffraction region
ϵ_{III}	Relative permittivity of backward diffraction region
E_I	Normalized electric field of backward diffraction region
E_3	Normalized electric field of forward diffraction region
t_g	Grating region thickness
R_i	Normalized amplitudes of the i^{th} reflected wave in backward diffraction region
T_i	Normalized amplitudes of the i^{th} transmitted wave in forward diffraction region
\bar{k}_{1i}	Wavevector of i^{th} reflected wave in backward diffraction region
\bar{k}_{3i}	Wavevector of i^{th} transmitted wave in forward diffraction region
\bar{k}_1	Allowed wavevector in cover (backward diffraction) region
\bar{k}_3	Allowed wavevector in substrate (forward diffraction) region
H_x	Tangential component of magnetic field
μ	Relative permeability
ω	Angular frequency

List of Symbols (Cont'd)

δ_{i0}	Kronecker delta function
DE_{1i}	Diffraction efficiency of i^{th} diffracted order in backward diffraction region
DE_{3i}	Diffraction efficiency of i^{th} diffracted order in forward diffraction region
$N_{eff,v}$	Effective refractive index of v^{th} waveguide mode
$\theta_{i,v}$	Angle of diffraction of v^{th} waveguide mode
α_v	Coupling coefficient of v^{th} mode
$\tilde{\gamma}_v$	Complex propagation constant of supported waveguide/grating mode
$\beta_{v,\text{mod}}$	Propagation constant of v^{th} mode in presence of grating index modulation
$\eta_{p,i}$	Preferential coupling ratio of i^{th} diffracted order in region p
$P_{p,i}$	Power coupled into i^{th} diffracted order in region p
DE_{output}	Output diffraction efficiency
DE_{input}	Input diffraction efficiency
P_i	Time average power flow normal to the waveguide of i^{th} diffracted order
I_{out}	Out-coupled intensity profile at grating surface
I_{in}	Gaussian input intensity profile at grating surface
w_{beam}	Gaussian beam width
x_o	Relative longitudinal location of Gaussian peak
E_{1w}	Electric field of interferometric recording beam #1
E_{2w}	Electric field of interferometric recording beam #2

List of Symbols (Cont'd)

k_{x1w}	Wavevector of interferometric recording beam #1 in grating region
k_{x2w}	Wavevector of interferometric recording beam #2 in grating region
$n_{wg,w}$	Refractive index of grating material at write wavelength
λ_w	Holographic write wavelength
n_{pw}	Prism refractive index at write wavelength
I_w	Intensity profile of interference pattern of two recording beams
A_{1w}	Amplitude of interferometric recording beam #1
A_{2w}	Amplitude of interferometric recording beam #2
δ_{shrink}	Percent decrease in grating thickness (shrink) during thermal cure
K_{xs}	x -component of grating vector accounting for shrinkage
K_{zs}	z -component of grating vector accounting for shrinkage
θ_{a_1}	Angle of incidence of beam #1 at air-prism interface with respect to normal of grating layer
θ_{a_2}	Angle of incidence of beam #2 at air-prism interface with respect to normal of grating layer
θ_{1w}	Angle of incidence of beam #1 at air-prism interface with respect to normal of prism
θ_{2w}	Angle of incidence of beam #2 at air-prism interface with respect to normal of prism
θ_{g1}	Angle of refraction of k_{1w} in grating region with respect to normal of grating layer
θ_{g2}	Angle of refraction of k_{2w} in grating region with respect to normal of grating layer
θ_{p1}	Angle of incidence of beam #1 at prism-grating interface with respect to normal of grating layer

List of Symbols (Cont'd)

θ_{p2}	Angle of incidence of beam #2 at prism-grating interface with respect to normal of grating layer
$\Delta\theta$	Angular offset between two recording beams
α_{TE}	Grating coupling coefficient for fundamental mode under TE polarized light
α_{TM}	Grating coupling coefficient for fundamental mode under TM polarized light
A_n	Cauchy coefficient
B_n	Cauchy coefficient
C_n	Cauchy coefficient
P_{wg}	Power in optical waveguide
α_{wg}	Propagation loss coefficient
α_{rad}	Radiation loss coefficient
α_{abs}	Absorption loss coefficient
α_{scat}	Scattering loss coefficient
SSR	Sum of the square of residuals
q_h	h^{th} data point
\hat{q}_h	h^{th} fitted response value
r_h	h^{th} residual difference between q_h and \hat{q}_h
h	Reference index
w_h	Residual weight
σ_h	Residual variance
r_{adj}	Adjusted residuals

List of Symbols (Cont'd)

v_h	h^{th} leverage factor
u_{adj}	Standardized adjusted residuals
$\backslash K$	Constant for standardized adjusted residuals
$\backslash s$	Constant for standardized adjusted residuals
w_h	Robust bisquare weights
θ_{y-j}	Y-junction branching output half angle
L_{taper}	Length of taper region, Y-splitter
R_{couple}	Radius of curvature, 3 dB coupler
L_{couple}	Length of coupling region, 3 dB coupler
L_{MMI}	Length of MMI region
w_{MMI}	Width of MMI region
N_{output}	Fanout of MMI device
d_{MMI}	Pitch between MMI output waveguides
$\sigma_{TE, TM}$	Polarization factor, MMI device
$L_{MMI, acceptable}$	Acceptable range of MMI device lengths
$w_{MMI, acceptable}$	Acceptable range of MMI device widths
DR	Dynamic range of MMI output
max_{count}	Maximum pixel brightness count
min_{count}	Minimum pixel brightness count
ΔP_{MMI}	MMI output power uniformity
$max_{area, outputs}$	Maximum pixel count summation of MMI output
$min_{area, outputs}$	Minimum pixel count summation of MMI output

List of Symbols (Cont'd)

A_{det}	Detector area
$\Delta x_{\Delta\lambda}$	Maximum longitudinal optical beam width under wavelength variations
Δx	Maximum longitudinal placement variations due to solder attach process
Δy	Maximum transverse placement variations due to solder attach process
z_f	Nominal focal plane of focusing grating coupler
Δz	Maximum vertical placement variations due to solder attach process
$\Delta\lambda$	Range of wavelength variations
t_{solder}	Solder ball height
$t_{package}$	Chip-level package thickness
t_{wiring}	Multi-level wiring network thickness
Δt_{solder}	Vertical bump deviations
$\Delta x_{\Delta\lambda}$	Longitudinal beam width of focusing grating coupler under placement, wavelength variations
R_{bend}	Bend radius of waveguide bend
$P_{loss,bend}$	Power loss for waveguide bend
t_{wg}	Waveguide thickness

List of Abbreviations

CMOS	Complementary Metal Oxide Semiconductor
SIMOX	Separation by Implantation of Oxygen
VCSEL	Vertical Cavity Surface Emitting Laser
AR	Anti-Reflection
BEOL	Back-End-Of-Line
OMCVD	Organo-Metallic Chemical Vapor Deposition
LED	Light Emitting Diode
I-MSM	Inverted Metal-Semiconductor-Metal
MCM-L	Multi-Chip Module Laminated
TAB	Tape Automated Bonded
OETC	Optoelectronics Technology Consortium
OSA	Optical Subassembly
FAB	Fiber Array Block
POLO	Parallel Optical Link Organization
QFP	Quad Flat-Pack
BGA	Ball Grid Array
PONI	Parallel Optics for Network Interconnects
POSA	Parallel Optical Sub-Assembly
OL	Open-Loop
CL	Closed-Loop
CLAC	Closed-Loop with Active Compensation
PLL	Phase-Locked Loop

List of Abbreviations (Cont'd)

VCO	Voltage-Controlled Oscillator
ITRS	International Technology Roadmap for Semiconductors
DOE	Diffractive Optical Element
TIR	Total Internal Reflection
RLC	Resistive-Inductive-Capacitive
RC	Resistive-Capacitive
ToF	Time-of-Flight
ADI	Alternating Direction Implicit
PNB	Polynorbornene
MSQ	Methylsilsesquioxane
TMSNB	Tri-Methyl Substituted Norbornene
BPM	Beam Propagation Method
PECVD	Plasma Enhanced Chemical Vapor Deposition
ESD	Electrostatic Discharge
TE	Transverse Electric
TM	Transverse Magnetic
RCWA	Rigorous Coupled Wave Analysis
TNU	Thickness Non-Uniformity Parameter
STS	Surface Technology Systems
VASE	Variable Angle Spectroscopic Ellipsometry
UV	Ultra-Violet
RBLLS	Robust Bisquare Linear Least Squares

List of Abbreviations (Cont'd)

MAD	Median Absolute Deviation
FWHM	Full Width at Half Max
DR	Dynamic Range
MMI	Multi-Mode Interference
FDTD	Finite Difference Time Domain
MSE	Mean Square Error

Summary

The concept of polyolithic integration of electrical and optical interconnect technologies is presented. The use of a two-grating, or grating-to-grating, coupling path for board-to-chip coupling of optical signals is proposed for fiber-to-the-chip and intra-chip optical clock distribution applications. An estimate for the increase in electrical I/O and substrate-level electrical interconnect layers required for a 40 Tb/s fiber-to-the-chip communication system using grating-to-grating board-to-chip coupling of optical signals is provided. An estimate of the ITRS technology generation within which alternate methods of intra-chip clock distribution are required is identified, and the strengths and weaknesses associated with different methods of optical clock distribution are summarized. A partition length between and routing area associated with on-chip optical waveguides and board-level electrical exterconnects is provided for signal distribution in gigascale microprocessors.

In addition, Avatrel 2190P is investigated as a candidate material for the creation of integrated optical waveguides and power splitters. Low-decomposition-temperature sacrificial polymers are used to construct chip-length embedded air-clad optical waveguides for on-chip signal and clock distribution. A wafer-level batch package exhibiting compatible electrical and optical I/O interconnects is presented, where two-material index-defined and air-clad waveguide/grating channels are fabricated and tested. Finally, grating-to-grating coupling over a quasi-free space coupling path is demonstrated and quantified for the first time to illustrate the feasibility of board-to-chip optical I/O in gigascale microprocessor systems.